

**Course Name** - High Speed Devices and Circuits

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**Institute Name** - IIT Madras

**Course Syllabus** -

1. Important parameters governing the high speed performance of devices and circuits:- Transit time of charge carriers, junction capacitances, ON-resistances and their dependence on the device geometry and size, carrier mobility, doping concentration and temperature. Contact resistance and interconnection/interlayer capacitances in the Integrated Electronics Circuits. (4 hours)
2. Silicon based MOSFET and BJT circuits for high speed operation and their limitations:- Emitter coupled Logic (ECL) and CMOS Logic circuits with scaled down devices. Silicon On Insulator (SOI) wafer preparation methods and SOI based devices and SOICMOS circuits for high speed low power applications. (8 hours)
3. Materials for high speed devices and circuits:- Merits of III –V binary and ternary compound semiconductors (GaAs, InP, InGaAs, AlGaAs ETC.), silicon-germanium alloys and silicon carbide for high speed devices, as compared to silicon based devices. Brief outline of the crystal structure, dopants and electrical properties such as carrier mobility, velocity versus electric field characteristics of these materials. Material and device process technique with these III-V and IV – IV semiconductors. (8 hours)
4. Metal semiconductor contacts and Metal Insulator Semiconductor and MOS devices: Native oxides of Compound semiconductors for MOS devices and the interface state density related issues. Metal semiconductor contacts, Schottky barrier diode. Thermionic Emission model for current transport and current-voltage (I-V) characteristics. Effect of interface states and interfacial thin electric layer on the Schottky barrier height and the I-V characteristics. (6 hours)
5. Metal semiconductor Field Effect Transistors (MESFETs): Pinch off voltage and threshold voltage of MESFETs. D.C. characteristics and analysis of drain current. Velocity overshoot effects and the related advantages of GaAs, InP and GaN based devices for high speed operation. Sub threshold characteristics, short channel effects and the performance of scaled down devices. (6 hours)
6. High Electron Mobility Transistors (HEMT): Hetero-junction devices. The generic Modulation Doped FET(MODFET) structure for high electron mobility realization. Principle of operation and the unique features of HEMT. InGaAs/InP HEMT structures. ( 6 hours)
7. Hetero junction Bipolar transistors (HBTs): Principle of operation and the benefits of hetero junction BJT for high speed applications. GaAs and InP based HBT device structure and the surface passivation for stable high gain high frequency performance. SiGe HBTs and the concept of strained layer devices. (6 hours)
8. High speed Circuits: GaAs Digital Integrated Circuits for high speed operation- Direct Coupled Field Effect Transistor Logic (DCFL), Schottky Diode FET Logic (SDFL), Buffered FET Logic(BFL). GaAs FET Amplifiers. Monolithic Microwave Integrated Circuits (MMICs) (4 hours)
9. High Frequency resonant – tunneling devices. Resonant-tunneling hot electron transistors and circuits. (2 hours)